

Features

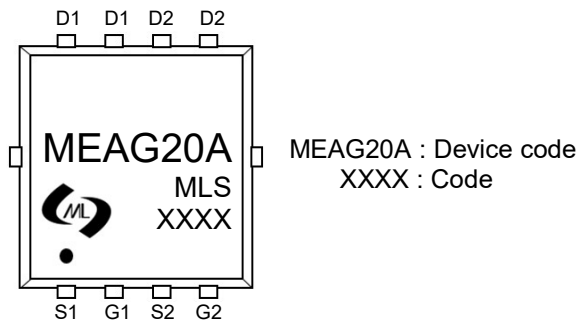
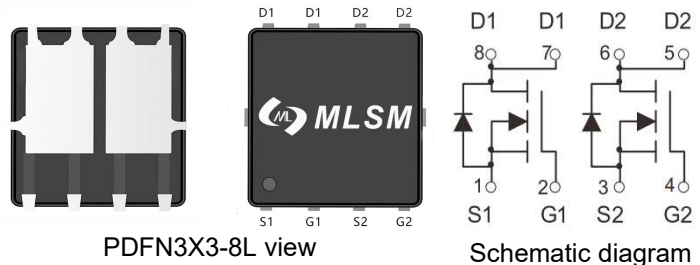
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
60V	30m Ω @10V	20A
	40m Ω @4.5V	

Application

- Power switching application



Marking and pin assignment

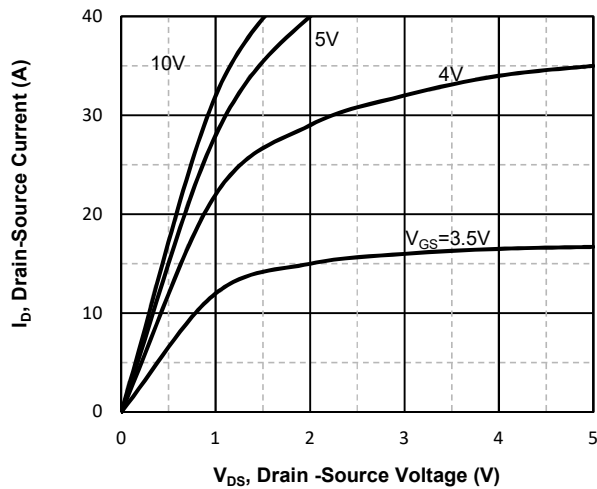
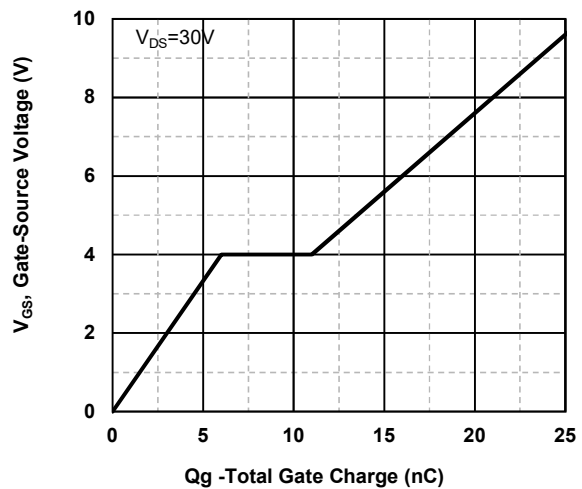
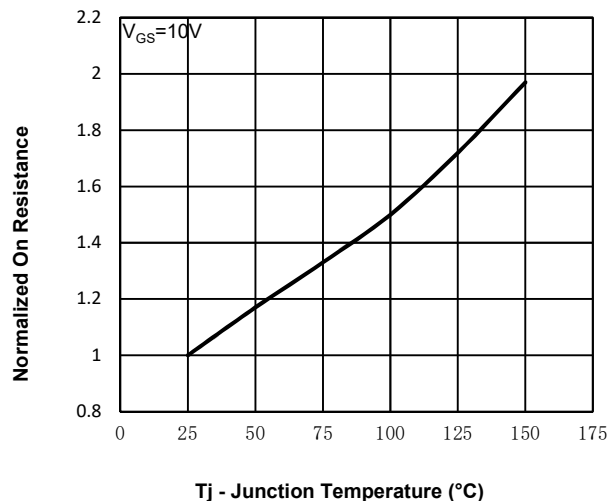
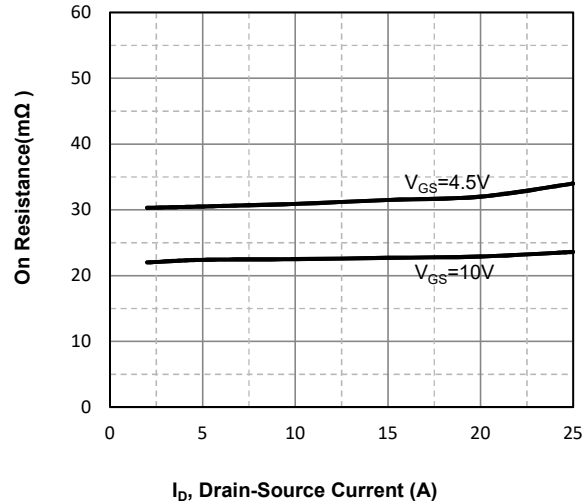
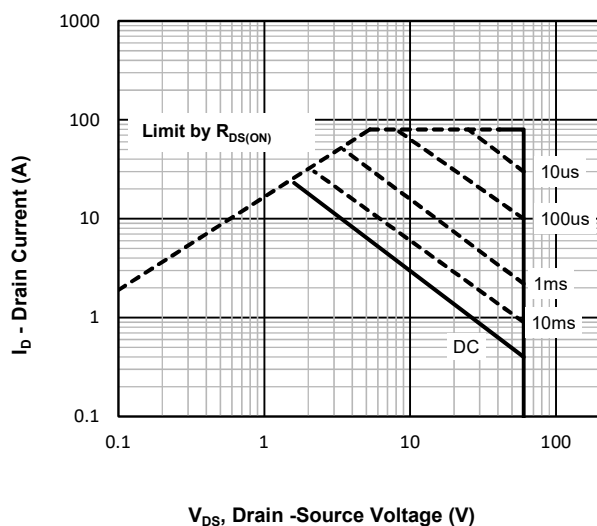
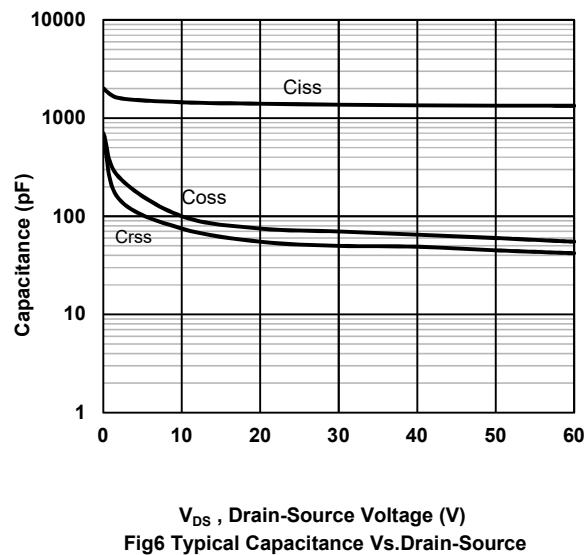


Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		60	V
V_{GS}	Gate-Source Voltage		± 20	V
T_J	Maximum Junction Temperature		150	$^{\circ}C$
T_{STG}	Storage Temperature Range		-50 to 155	$^{\circ}C$
I_S	Diode Continuous Forward Current	$T_c=25^{\circ}C$	20	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	$T_c=25^{\circ}C$	80	A
I_D	Continuous Drain Current	$T_c=25^{\circ}C$	20	A
P_D	Maximum Power Dissipation	$T_c=25^{\circ}C$	3.6	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		85	$^{\circ}C/W$

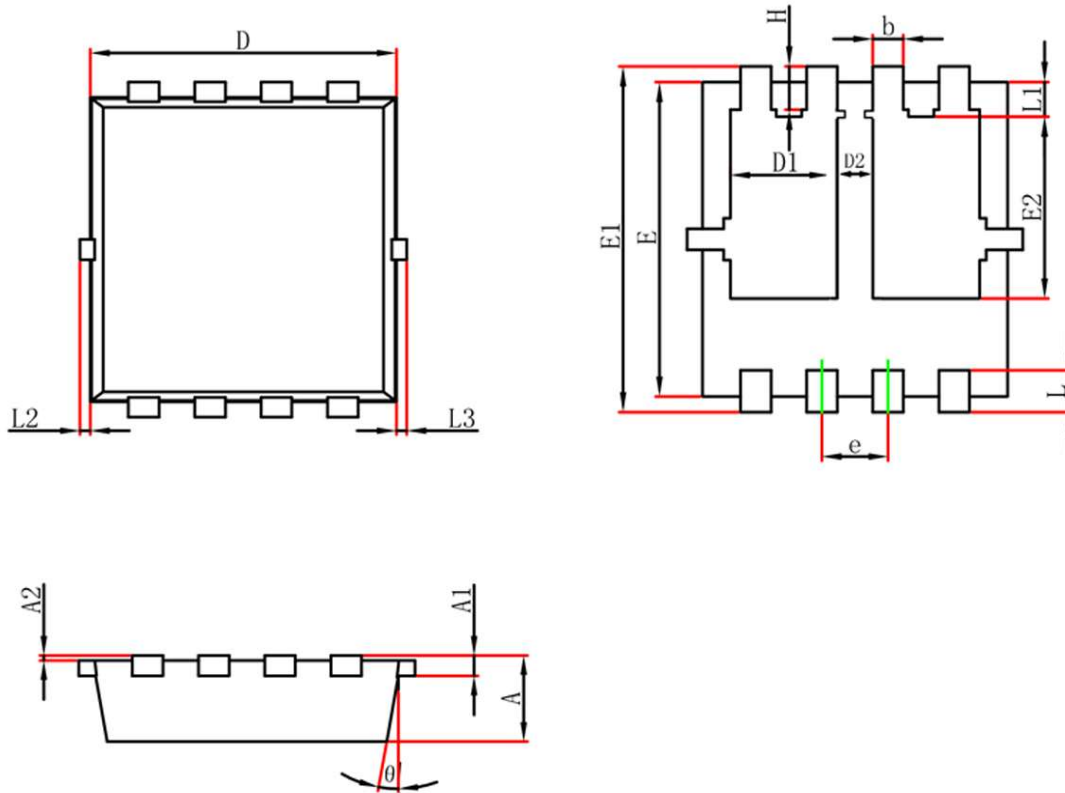
Ordering Information (Example)						
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MEAG20A	PDFN3X3-8L	MEAG20 A	5,000	10,000	70,000	13"reel



Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	22	30	mΩ
		V _{GS} =4.5V, I _D =15A	--	30	40	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	1050	--	pF
C _{OSS}	Output Capacitance		--	65	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	55	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =30V, I _D =20A, V _{GS} =10V	--	26	--	nC
Q _{gs}	Gate Source Charge		--	5.7	--	nC
Q _{gd}	Gate Drain Charge		--	5.2	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =20A, V _{GS} =10V, R _G =3Ω	--	8.4	--	nS
t _r	Turn-on Rise Time		--	8.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	36	--	nS
t _f	Turn-Off Fall Time		--	5	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =20A	--	0.8	1.2	V

Typical Operating Characteristics

Fig1. Typical Output Characteristics

Fig2. Typical Gate Charge Vs. Gate-Source Voltage

Fig3. Normalized On-Resistance Vs. Temperature

Fig4. On-Resistance Vs. Drain-Source Current

Fig5. Maximum Safe Operating Area

Fig6. Typical Capacitance Vs. Drain-Source

PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	3.050	3.150	0.121	0.125
D1	0.985	1.085	0.039	0.043
D2	0.330	0.430	0.013	0.017
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.280	0.380	0.011	0.015
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.350	0.450	0.014	0.018
θ	9°	13°	10°	12°